

The Inaugural Reliability Experts Forum at IIRW 2018

IEEE INTERNATIONAL INTEGRATED RELIABILITY WORKSHOP

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RELIABILITY WORKSHOP



October 9, 2018

**Stanford Sierra Conference
Center
Fallen Leaf Lake,
CA, USA**

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Globalfoundries, USA

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Souvik Mahapatra
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EDS Device Reliability Physics Committee member:

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The International Integrated Reliability workshop (IIRW 2018) and the IEEE Electron Device Society (EDS) are pleased to announce the inaugural “Reliability Experts Forum” which will be held on Tuesday, October 9th as part of the IIRW 2018 technical program, which is taking place at the Stanford Sierra Conference center, South Lake Tahoe, USA, from October 7th to 11th.

The 1-day event aims to assemble the top reliability experts to discuss the current understanding and the challenges facing the three main transistor reliability mechanisms -- TDDB, BTI and Hot Carrier degradation. The three panel discussions will focus on device physics and the reliability models associated with each mechanism. Each session will be ran by a moderator, and animated by multiple panelists.

More than forty world-renown reliability experts are invited to share their views and enrich the discussion. The names of the moderators and panelist will be published, June 15th at www.iirw.org

**For more information please visit www.iirw.org, or contact the technical program chair:
Zakariae Chbili
GLOBALFOUNDRIES, USA
email: iirw2018@gmail.com**